SS8050

Plastic-Encapsulate Transistors

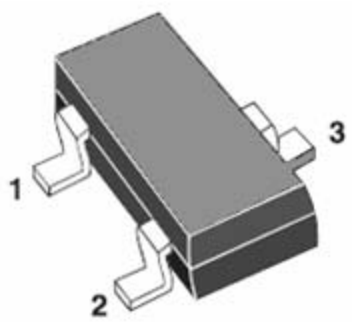
Features

◆Power dissipation
P_{CM}:0.3W(T_A=25°C)
◆Collector current
I_C:1.5A
◆Collector-base voltage
$V_{(BR)CBO}$:40V
◆Opcrating and storage junction temperature range
T_J,T_{STG}:-55°C to +150°C

Marking:

Y1

SOT-23



1.BASE 2.EMITTER 3.COLLECTOR

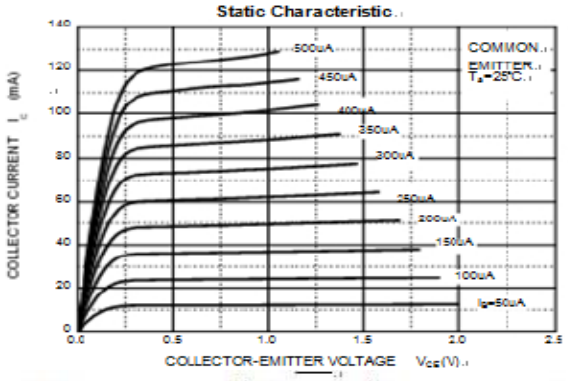
Electrical Characteristics(T_A =25°C unless otherwise specjfied):

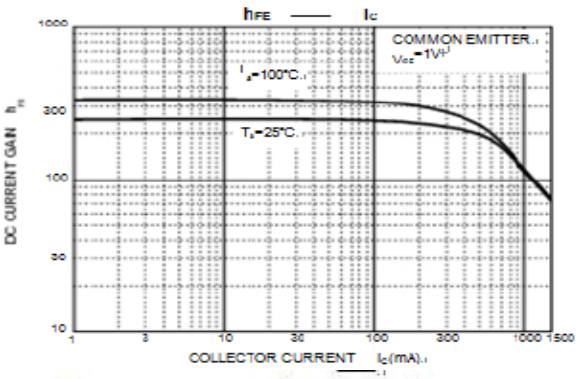
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100uA,I_E=0	40			V
Collector-emitre breakdown voltage	$V_{(BR)CEO}$	I_C=0.1mA,I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100uA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0			0.1	uA
Collector cut-off current	I_{CEO}	V_{CB}=20V,I_E=0			0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	uA
DC current gain	$h_{FE(1)}$	V_{CE}=1V,I_C=100mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V,I_C=800mA	40			
Collector-emittre saturation voltage	$V_{CE(sat)}$	I_C=800mA,I_B=80mA			0.5	V
Base-emitre saturation voltage	$V_{BE(sat)}$	I_C=800mA,I_B=80mA			1.2	V
Transition frequency	f_T	V_{CE}=10V,I_C=50mA F=30MHZ	100			MHZ

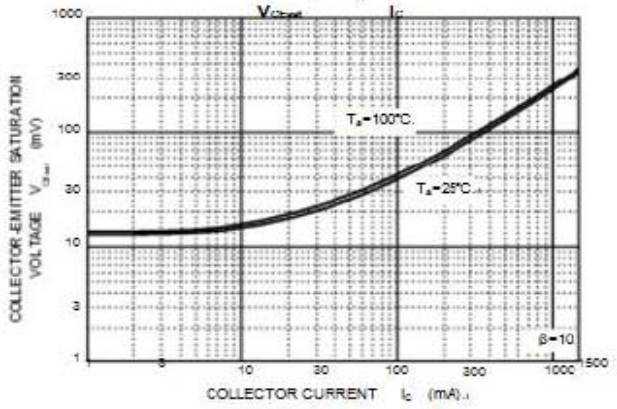
Classification of $h_{FE(1)}$

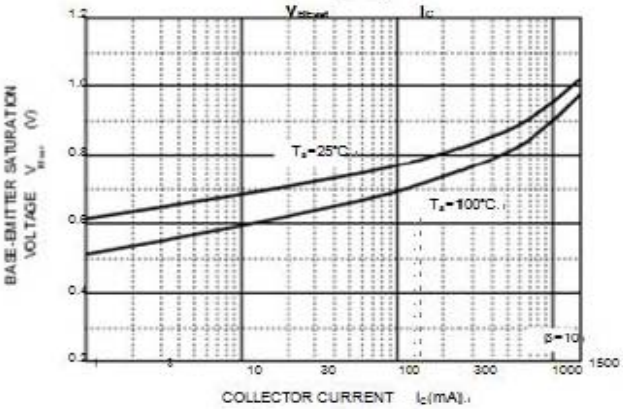
Rank	L	H	J
Range	120～200	200～350	300～400

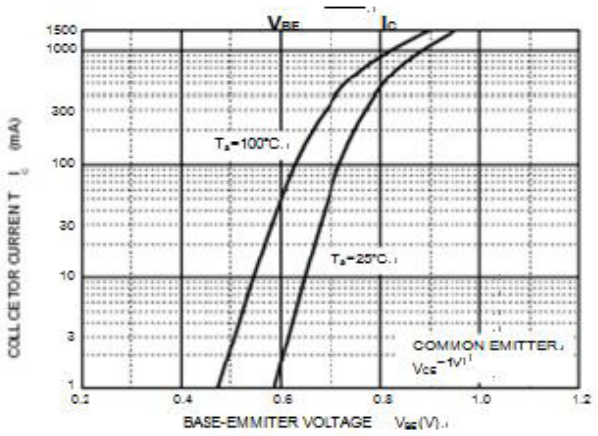
Ratings and Characteristic Curves T_A=25°C unless otherwise noted

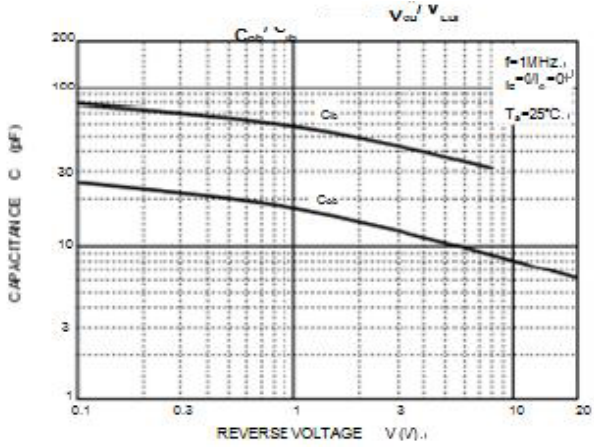


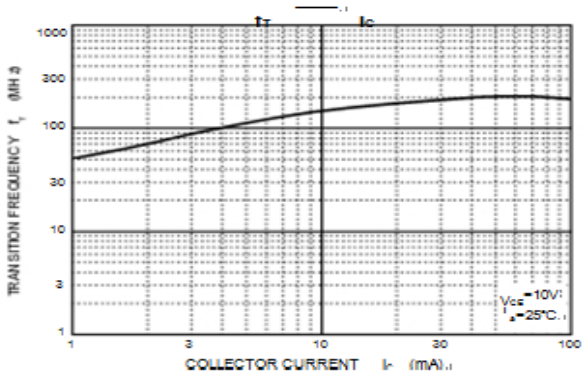


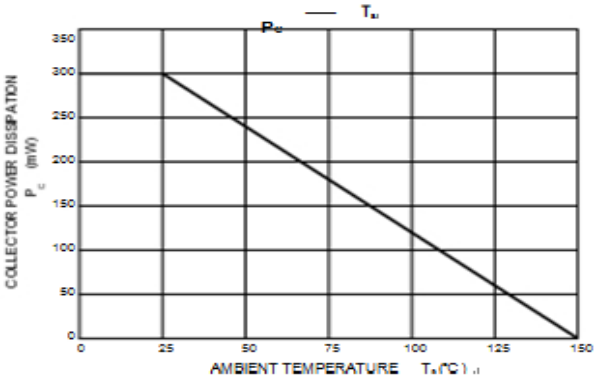












SOT-23 MECHANICAL DATA